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- (71) Applicant (for all designated States except US): INTENSE PHOTONICS LTD [GB/GB]; 4 Stanley Boulevard, Hamilton International Technology Park, High Blantyre, Glasgow G72 0BN (GB).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): QIU, Bocang [CN/GB]; Intense Photonics Ltd, 4 Stanley Boulevard, Hamilton International Technology Park, High Blantyre, Glasgow G72 0BN (GB).
- (74) Agent: CHARIG, Raymond; Eric Potter Clarkson, Park View House, 58 The Ropewalk, Nottingham NG1 5DD (GB).

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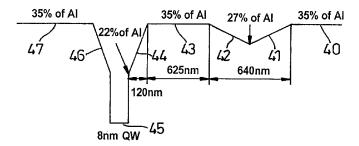
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(54) Title: CONTROL OF OUTPUT BEAM DIVERGENCE IN A SEMICONDUCTOR WAVEGUIDE DEVICE



(57) Abstract: A semiconductor laser device incorporates a beam control layer (42, 41) for reducing far field and beam divergence. Within the beam control layer, a physical property of the semiconductor material varies as a function of depth through, the beam control layer, by provision of a first sub-layer (42) in which the property varies gradually from a first level to a second level, and a second sub-layer (41) in which the property varies from said second level to a third level. In the preferred arrangement, the conduction band edge of the semiconductor has a V-shaped profile through the beam control layer.